

**P-Ch MOSFET** 

# **General Description**

The WSD90P06DN56 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSD90P06DN56 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

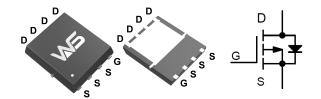
### **Product Summery**

BVDSS	RDSON	ID
-60V	10mΩ	-90A

# **Applications**

- Power Management
- Load Switch

# DFN5X6\_8L Pin Configuration



# **Absolute Maximum Ratings**

Symbol	Parameter Rating		Units
$V_{DS}$	Drain-Source Voltage	Drain-Source Voltage -60	
$V_{GS}$	Gate-Source Voltage	Gate-Source Voltage ±20	
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, -V <sub>GS</sub> @ -10V	-90	Α
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, -V <sub>GS</sub> @ -10V -40		А
I <sub>DM</sub>	Pulsed Drain Current	Drain Current -190	
P <sub>D</sub> @T <sub>C</sub> =25℃	c=25℃ Total Power Dissipation 96		W
T <sub>STG</sub>	Storage Temperature Range	Storage Temperature Range -55 to 150	
TJ	T <sub>J</sub> Operating Junction Temperature Range -55 to 150		$^{\circ}$

### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>0JA</sub>	Thermal Resistance Junction-Ambient		62	°C/W
R <sub>0JC</sub>	Thermal Resistance Junction-Case		1.3	°C/W



# P-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-60			V
В	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V , I <sub>D</sub> =-18A		10	14	m()
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-12A		13	18	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=-250uA$	-1.1	-1.8	-2.5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{DS}$ =-48V , $V_{GS}$ =0V , $T_J$ =25 $^{\circ}$ C			1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm 20V$ , $V_{DS}$ = $0V$			±100	nA
Qg	Total Gate Charge	Voc. 20 V. Voc. 40 V		89		
$Q_{gs}$	Gate-Source Charge	VDS = -30 V, VGS = -10 V, ID = -17A		12		nC
$Q_gd$	Gate-Drain Charge			32		
T <sub>d(on)</sub>	Turn-On Delay Time	VDD = -30 V,		15		
Tr	Rise Time	$RL = 30\Omega$ , $ID = -1$ A,		13		no
$T_{d(off)}$	Turn-Off Delay Time	VGEN = -10 V, $R_g = 6\Omega$		110		ns
T <sub>f</sub>	Fall Time			60		
C <sub>iss</sub>	Input Capacitance	Vps=-30V,Vgs=0V, f=1.0MHz		4066		
Coss	Output Capacitance			501		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			291		

### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	T <sub>C</sub> =25 °C			-40	Α
$V_{SD}$	Diode Forward Voltage	$V_{GS}$ =0 $V$ , $I_{S}$ =-1 $A$ , $T_{J}$ =25 $^{\circ}$ C			-1.2	V

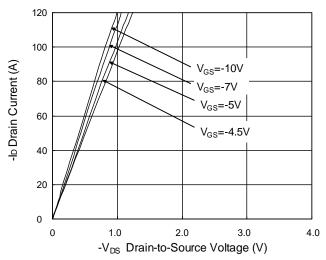
A: The value of Regain measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with Ta=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.

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# P-Channel Typical Characteristics



**Fig.1 Typical Output Characteristics** 

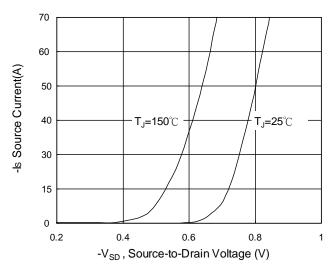


Fig.3 Source Drain Forward Characteristics

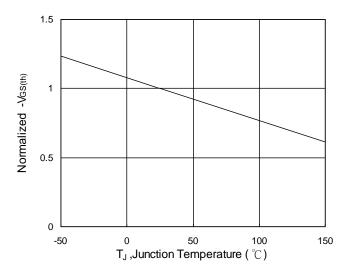


Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$ 

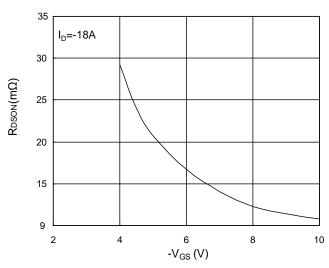


Fig.2 On-Resistance vs G-S Voltage

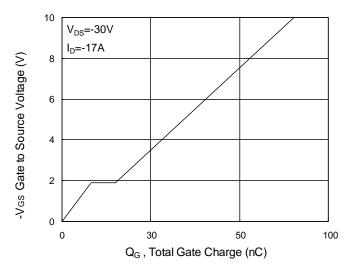


Fig.4 Gate-Charge Characteristics

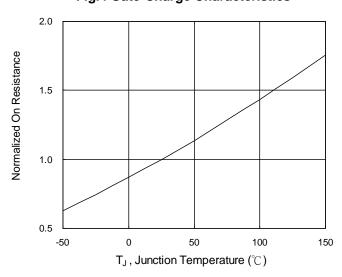


Fig.6 Normalized R<sub>DSON</sub> vs T<sub>J</sub>



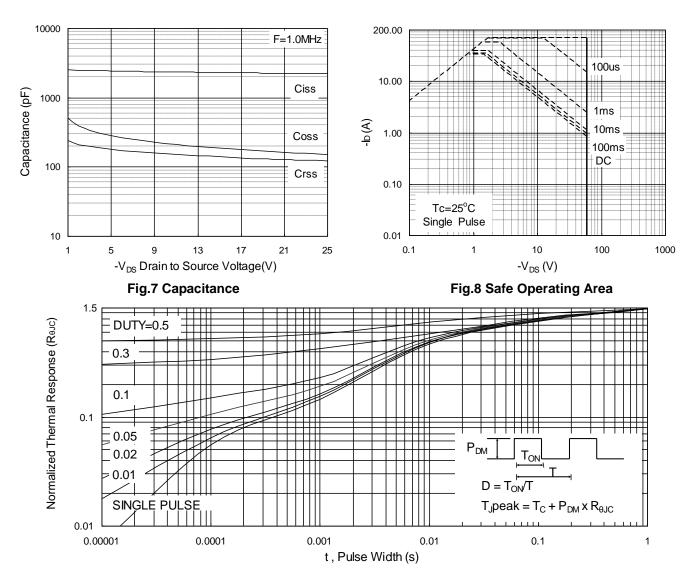


Fig.9 Normalized Maximum Transient Thermal Impedance

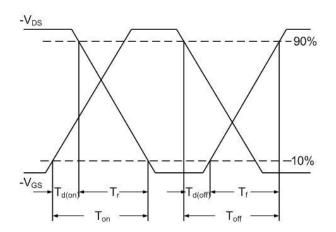


Fig.10 Switching Time Waveform

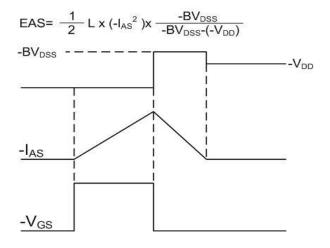


Fig.11 Unclamped Inductive Waveform



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